

# PHYSICS OF SEMICONDUCTORS

30th International Conference on the Physics of Semiconductors

*Seoul, Korea 25 – 30 July 2010*

■ PART A

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**AIP**  
American Institute  
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**Melville, New York, 2011**

**AIP | CONFERENCE PROCEEDINGS ■ 1399**

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L.C. Catalog Card No. 2011939514

ISBN 978-0-7354-0970-5 (Part A)\*Qtki kpciRtlpv+

ISBN 978-0-7354-1001-5 (Part B)\*Qtki kpciRtlpv+

ISBN 978-0-7354-1002-2 (2 Volume Set)\*Qtki kpciRtlpv+

ISBN 978-0-7354-0997-2 (DVD)

ISSN 0094-243X

Printed in the United States of America

*AIP Conference Proceedings, Volume 1399*  
**Physics of Semiconductors**  
**30th International Conference on the Physics of Semiconductors**

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